

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2001-085408  
(43)Date of publication of application : 30.03.2001

(51)Int.Cl. H01L 21/3065  
H01L 27/108  
H01L 21/8242

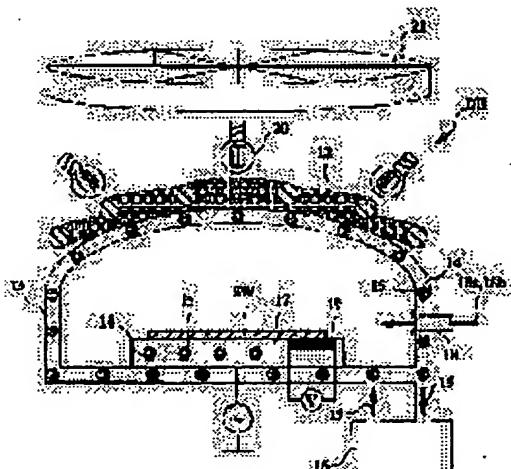
(21)Application number : 11-259239 (71)Applicant : HITACHI LTD  
(22)Date of filing : 13.09.1999 (72)Inventor : TAKAHASHI OSAMU  
SUZUKI SHINICHI  
KUROKI KEIJI

## (54) METHOD AND DEVICE FOR MANUFACTURING SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE

### (57)Abstract:

PROBLEM TO BE SOLVED: To provide a technology that can reduce the manufacturing cost of a semiconductor integrated circuit device.

SOLUTION: In a method for manufacturing semiconductor integrated circuit device, a W film formed on a wafer SW is etched by heating the wafer SW to about 100–250° C by using all or part of infrared lamps 20, a temperature-adjusting liquid, a heating gas 18a, and a Peltier element 19. Then, a polycrystalline silicon film formed on the wafer SW is etched continuously by cooling the wafer SW to about -30 to 80° C by using all or part of the temperature-adjusting liquid 15, a cooling gas 18b, and the Peltier element 19.



## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]